

MJE13005DT3 (3DD13005DT3)

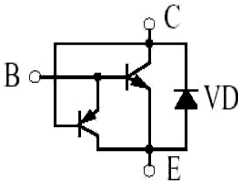
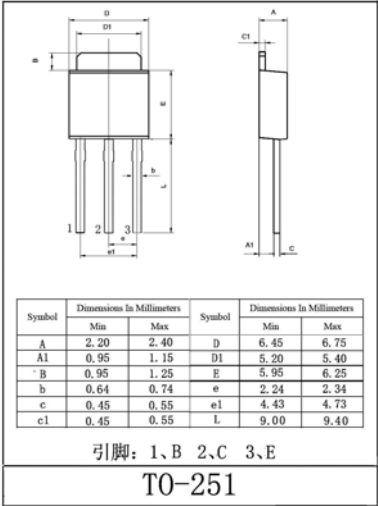
硅 NPN 半导体三极管/SILICON NPN TRANSISTOR

用途:用于高频电子照明电路、开关及开关电源。

Purpose: High frequency electronic lighting, switching power supply applications.

极限参数/Absolute maximum ratings(Ta=25℃)

参数符号 Symbol	数值 Rating	单位 Unit
V _{CB0}	700	V
V _{CE0}	400	V
V _{EB0}	9	V
I _C	4	A
I _B	2	A
P _c (Ta=25℃)	1.2	W
P _c (Tc=25℃)	50	W
T _j	150	℃
T _{stg}	-55~150	℃

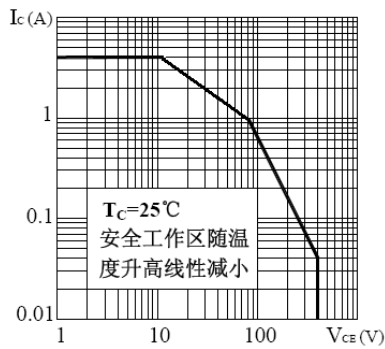


电性能参数/Electrical characteristics(Ta=25℃)

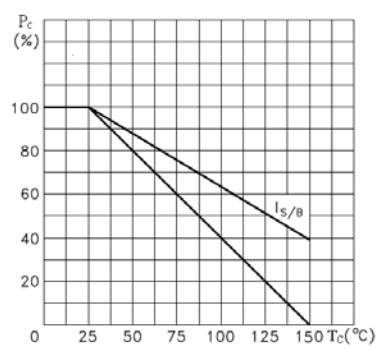
参数符号 Symbol	测试条件 Test condition		数值 Rating			单位 Unit
			最小值 Min	典型值 Typ	最大值 Max	
V _{CB0}	I _C =1mA	I _E =0	700			V
V _{CE0}	I _C =10mA	I _B =0	400			V
V _{EB0}	I _E =1mA	I _C =0	9			V
I _{CB0}	V _{CB} =700V	I _E =0			0.1	mA
I _{CE0}	V _{CE} =400V	I _B =0			0.1	mA
I _{EB0}	V _{EB} =9.0V	I _C =0			0.1	mA
h _{FE(1)}	V _{CE} =5.0V	I _C =1.0A	15		30	
h _{FE(2)}	V _{CE} =5.0V	I _C =2.0A	8.0		40	
V _{CE(sat)(1)}	I _C =1.0A	I _B =0.2A			1.0	V
V _{CE(sat)(2)}	I _C =2.5A	I _B =0.5A			1.5	V
V _{CE(sat)(3)}	I _C =0.5A	I _B =0.1A			0.7	V
V _{BE(sat)(1)}	I _C =1.0A	I _B =0.2A			1.2	V
V _{BE(sat)(2)}	I _C =2.5A	I _B =0.5A			1.3	V
C _{ob}	V _{CB} =10V	f=1MHz		65		pF
f _T	V _{CE} =10V	I _C =0.5A	f=1MHz	7.0		MHz
t _f	V _{CE} =5.0V I _C =0.5A (UI9600)				0.8	μs
t _s			2.0		3.5	μs

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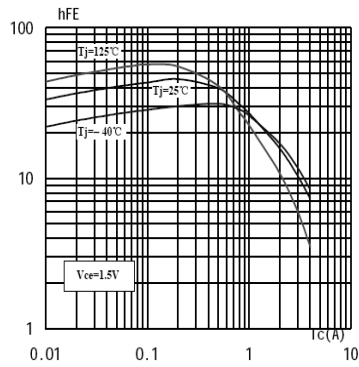
SOA (DC)



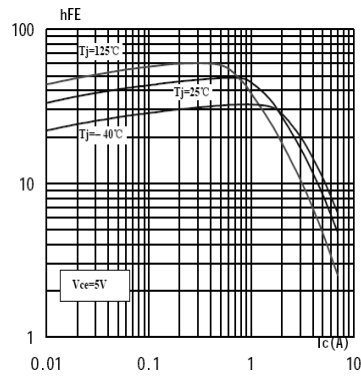
P_c-T_c



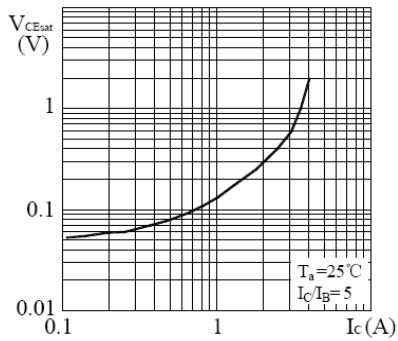
$h_{FE}-I_c$



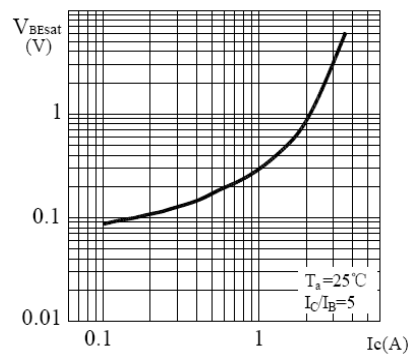
$h_{FE}-I_c$



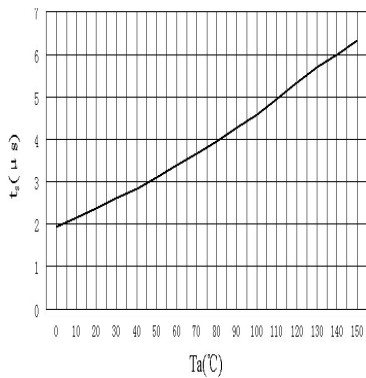
$V_{ces}-I_c$



$V_{bes}-I_c$



t_s-Ta



$h_{FE}-T_a$

